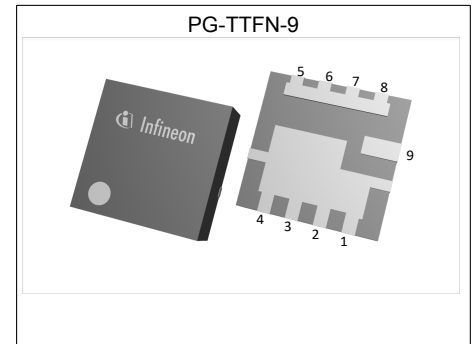


# MOSFET

## OptiMOS™ 7 Power-Transistor, 15 V

### Features

- N-channel, logic level
- Very low on-resistance  $R_{DS(on)}$
- Superior thermal resistance
- 100% avalanche tested
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21
- Optimized for high performance SMPS, e.g. synchronous rectification

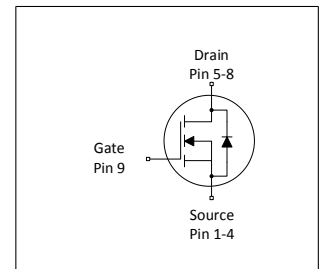


### Product validation

Fully qualified according to JEDEC for Industrial Applications

**Table 1 Key Performance Parameters**

Parameter	Value	Unit
$V_{DS}$	15	V
$R_{DS(on),max}$	0.45	m $\Omega$
$I_D$	379	A
$Q_{oss}$	27	nC
$Q_G$	29	nC



RoHS

Type / Ordering Code	Package	Marking	Related Links
IQE004NE1LM7CG	PG-TTFN-9	004E1C7	-

## Table of Contents

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## 1 Maximum ratings

at  $T_A=25\text{ °C}$ , unless otherwise specified

**Table 2 Maximum ratings**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current <sup>1)</sup>	$I_D$	-	-	379 240 58	A	$V_{GS}=7\text{ V}$ , $T_C=25\text{ °C}$ $V_{GS}=7\text{ V}$ , $T_C=100\text{ °C}$ $V_{GS}=7\text{ V}$ , $T_A=25\text{ °C}$ , $R_{thJA}=60\text{ °C/W}^2)$
Pulsed drain current <sup>3)</sup>	$I_{D,pulse}$	-	-	1516	A	$T_A=25\text{ °C}$
Avalanche energy, single pulse <sup>4)</sup>	$E_{AS}$	-	-	859	mJ	$I_D=20\text{ A}$ , $R_{GS}=25\text{ }\Omega$
Recommended gate source voltage	$V_{GS}$	-7	-	7	V	-
Gate source voltage, transient	$V_{GS,AC}$	-8	-	8	V	$t_{pulse}<20\text{ ns}$
Power dissipation	$P_{tot}$	-	-	89 2.1	W	$T_C=25\text{ °C}$ $T_A=25\text{ °C}$ , $R_{thJA}=60\text{ °C/W}^2)$
Operating and storage temperature	$T_j, T_{stg}$	-55	-	150	°C	-

## 2 Thermal characteristics

**Table 3 Thermal characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	$R_{thJC}$	-	-	1.4	°C/W	-
Thermal resistance, junction - ambient, 6 cm <sup>2</sup> cooling area <sup>5)</sup>	$R_{thJA}$	-	-	60	°C/W	-

<sup>1)</sup> Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

<sup>2)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 µm thick) copper area for source connection. PCB is vertical in still air.

<sup>3)</sup> See Diagram 3 for more detailed information

<sup>4)</sup> See Diagram 13 for more detailed information

<sup>5)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70 µm thick) copper area for connection. PCB is vertical in still air.

### 3 Electrical characteristics

at  $T_j=25\text{ °C}$ , unless otherwise specified

**Table 4 Static characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	15	-	-	V	$V_{GS}=0\text{ V}$ , $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	1.2	1.6	2.0	V	$V_{DS}=V_{GS}$ , $I_D=432\text{ }\mu\text{A}$
Zero gate voltage drain current	$I_{DSS}$	-	0.1 10	1 100	$\mu\text{A}$	$V_{DS}=12\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=25\text{ °C}$ $V_{DS}=12\text{ V}$ , $V_{GS}=0\text{ V}$ , $T_j=125\text{ °C}$
Gate-source leakage current	$I_{GSS}$	-	10	100	nA	$V_{GS}=7\text{ V}$ , $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.37 0.47	0.45 0.57	m $\Omega$	$V_{GS}=7\text{ V}$ , $I_D=30\text{ A}$ $V_{GS}=4.5\text{ V}$ , $I_D=20\text{ A}$
Gate resistance	$R_G$	-	0.4	-	$\Omega$	-
Transconductance	$g_{fs}$	85	170	-	S	$ V_{DS} \geq 2 I_D /R_{DS(on)max}$ , $I_D=30\text{ A}$

**Table 5 Dynamic characteristics**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	$C_{iss}$	-	4800	6240	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=7.5\text{ V}$ , $f=1\text{ MHz}$
Output capacitance <sup>1)</sup>	$C_{oss}$	-	2600	3380	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=7.5\text{ V}$ , $f=1\text{ MHz}$
Reverse transfer capacitance <sup>1)</sup>	$C_{rss}$	-	260	455	pF	$V_{GS}=0\text{ V}$ , $V_{DS}=7.5\text{ V}$ , $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	9	-	ns	$V_{DD}=7.5\text{ V}$ , $V_{GS}=7\text{ V}$ , $I_D=30\text{ A}$ , $R_{G,ext}=1.6\text{ }\Omega$
Rise time	$t_r$	-	2	-	ns	$V_{DD}=7.5\text{ V}$ , $V_{GS}=7\text{ V}$ , $I_D=30\text{ A}$ , $R_{G,ext}=1.6\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	21	-	ns	$V_{DD}=7.5\text{ V}$ , $V_{GS}=7\text{ V}$ , $I_D=30\text{ A}$ , $R_{G,ext}=1.6\text{ }\Omega$
Fall time	$t_f$	-	4	-	ns	$V_{DD}=7.5\text{ V}$ , $V_{GS}=7\text{ V}$ , $I_D=30\text{ A}$ , $R_{G,ext}=1.6\text{ }\Omega$

**Table 6 Gate charge characteristics<sup>2)</sup>**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge <sup>1)</sup>	$Q_{gs}$	-	13	18.8	nC	$V_{DD}=7.5\text{ V}$ , $I_D=30\text{ A}$ , $V_{GS}=0\text{ to }4.5\text{ V}$
Gate charge at threshold <sup>1)</sup>	$Q_{g(th)}$	-	7.6	11	nC	$V_{DD}=7.5\text{ V}$ , $I_D=30\text{ A}$ , $V_{GS}=0\text{ to }4.5\text{ V}$
Gate to drain charge <sup>1)</sup>	$Q_{gd}$	-	5.7	8.5	nC	$V_{DD}=7.5\text{ V}$ , $I_D=30\text{ A}$ , $V_{GS}=0\text{ to }4.5\text{ V}$
Switching charge	$Q_{sw}$	-	11.1	-	nC	$V_{DD}=7.5\text{ V}$ , $I_D=30\text{ A}$ , $V_{GS}=0\text{ to }4.5\text{ V}$
Gate charge total <sup>1)</sup>	$Q_g$	-	29	36	nC	$V_{DD}=7.5\text{ V}$ , $I_D=30\text{ A}$ , $V_{GS}=0\text{ to }4.5\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	2.7	-	V	$V_{DD}=7.5\text{ V}$ , $I_D=30\text{ A}$ , $V_{GS}=0\text{ to }4.5\text{ V}$
Gate charge total <sup>1)</sup>	$Q_g$	-	44	55	nC	$V_{DD}=7.5\text{ V}$ , $I_D=30\text{ A}$ , $V_{GS}=0\text{ to }7\text{ V}$
Output charge <sup>1)</sup>	$Q_{oss}$	-	27	36	nC	$V_{DS}=7.5\text{ V}$ , $V_{GS}=0\text{ V}$

<sup>1)</sup> Defined by design. Not subject to production test.

<sup>2)</sup> See "Gate charge waveforms" for parameter definition

**Table 7 Reverse diode**

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	$I_S$	-	-	87	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	1516	A	$T_C=25\text{ °C}$
Diode forward voltage	$V_{SD}$	-	0.76	1.0	V	$V_{GS}=0\text{ V}, I_F=30\text{ A}, T_j=25\text{ °C}$
Reverse recovery time <sup>1)</sup>	$t_{rr}$	-	31	62	ns	$V_R=7.5\text{ V}, I_F=30\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge <sup>1)</sup>	$Q_{rr}$	-	24	48	nC	$V_R=7.5\text{ V}, I_F=30\text{ A}, di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery time <sup>1)</sup>	$t_{rr}$	-	25	50	ns	$V_R=7.5\text{ V}, I_F=30\text{ A}, di_F/dt=300\text{ A}/\mu\text{s}$
Reverse recovery charge <sup>1)</sup>	$Q_{rr}$	-	49	98	nC	$V_R=7.5\text{ V}, I_F=30\text{ A}, di_F/dt=300\text{ A}/\mu\text{s}$

<sup>1)</sup> Defined by design. Not subject to production test.

### 4 Electrical characteristics diagrams

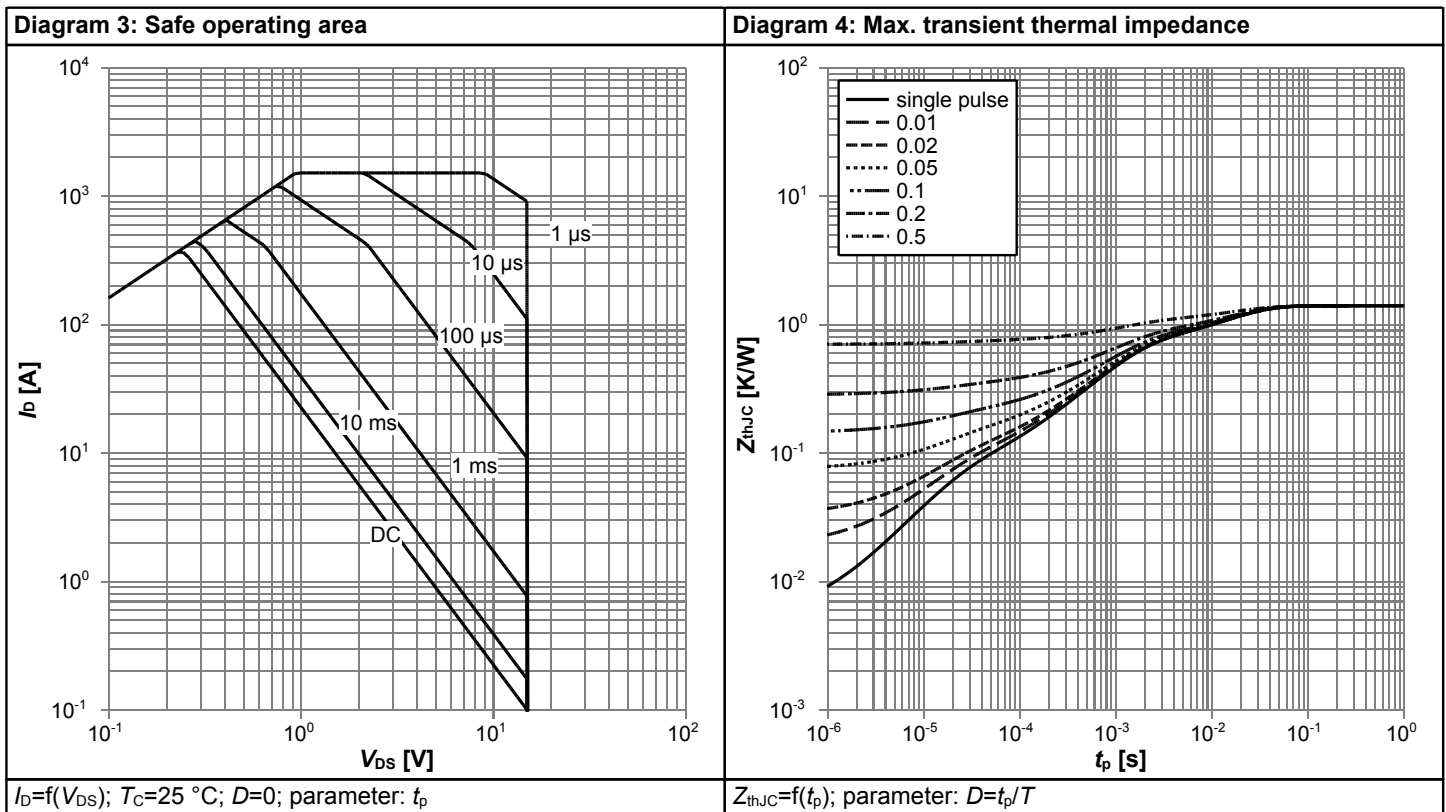
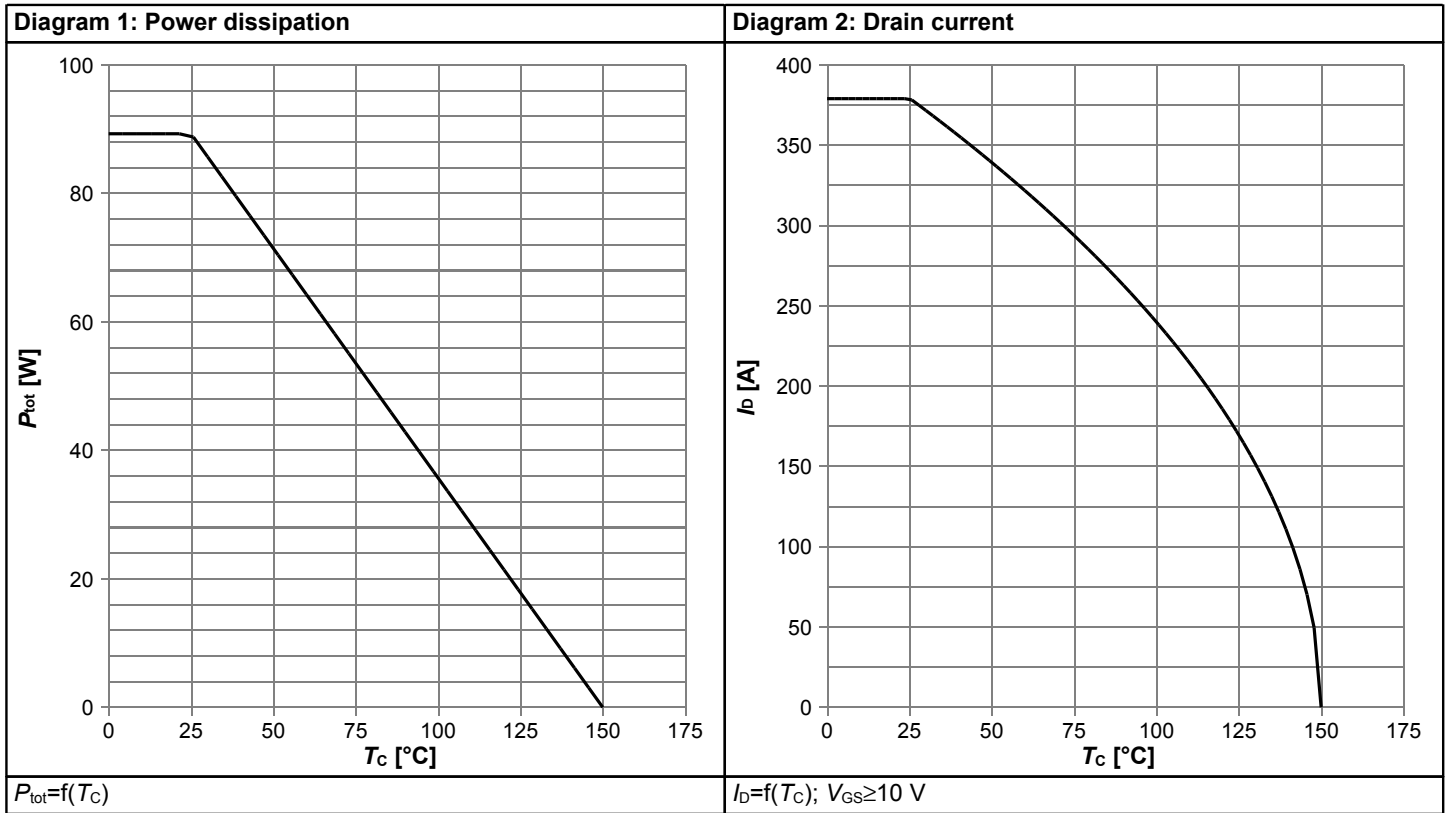
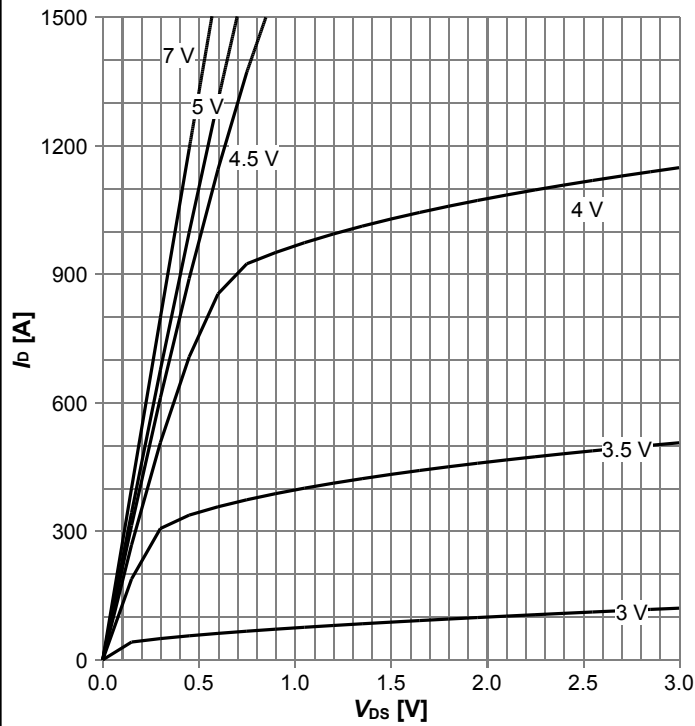
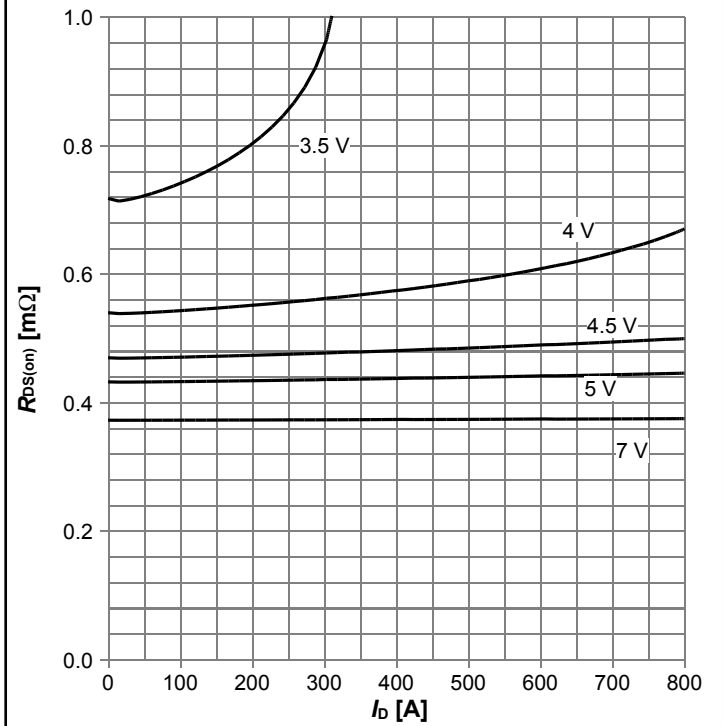


Diagram 5: Typ. output characteristics



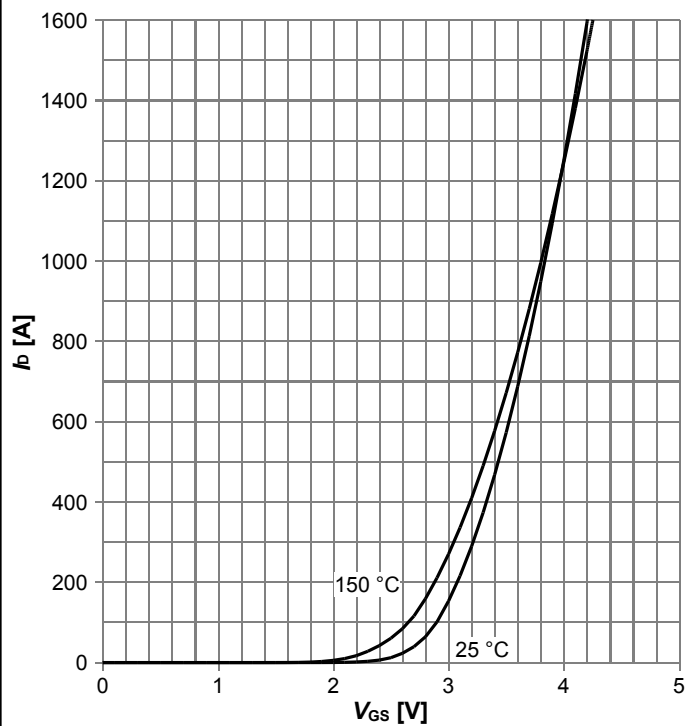
$I_D = f(V_{DS})$ ,  $T_j = 25\text{ °C}$ ; parameter:  $V_{GS}$

Diagram 6: Typ. drain-source on resistance



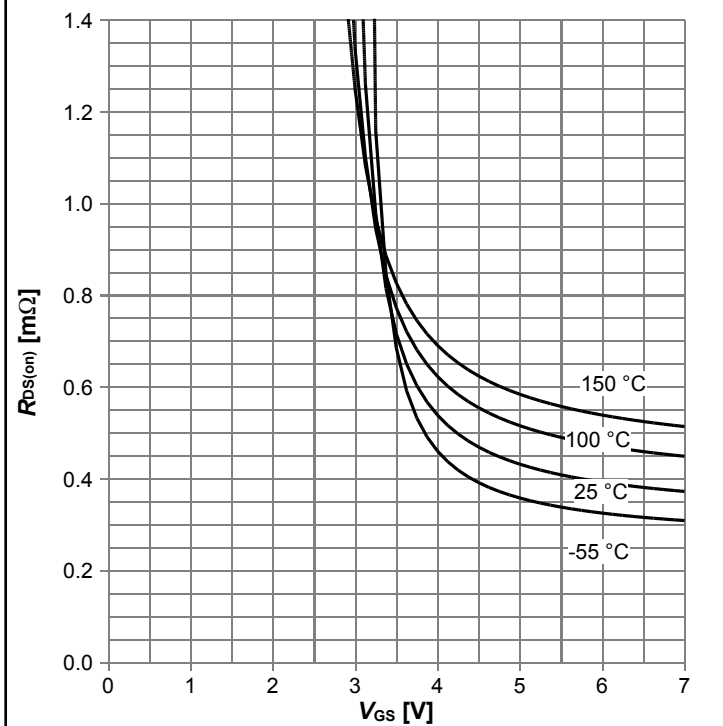
$R_{DS(on)} = f(I_D)$ ,  $T_j = 25\text{ °C}$ ; parameter:  $V_{GS}$

Diagram 7: Typ. transfer characteristics



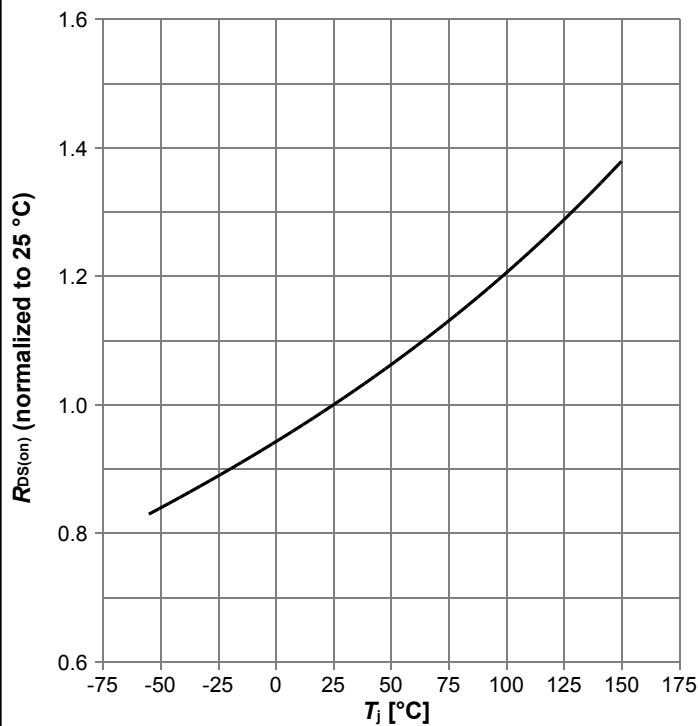
$I_D = f(V_{GS})$ ,  $|V_{DS}| > 2|I_D| R_{DS(on)max}$ ; parameter:  $T_j$

Diagram 8: Typ. drain-source on resistance



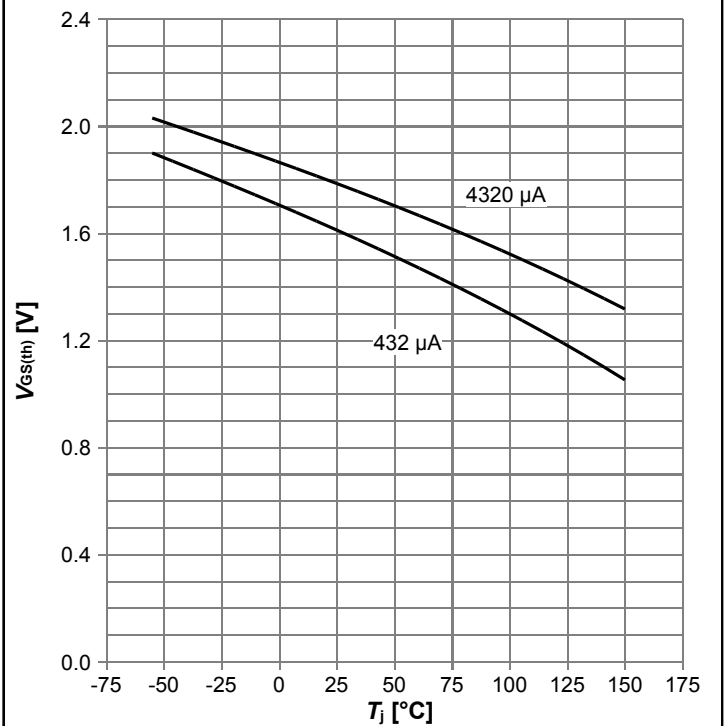
$R_{DS(on)} = f(V_{GS})$ ,  $I_D = 30\text{ A}$ ; parameter:  $T_j$

Diagram 9: Normalized drain-source on resistance



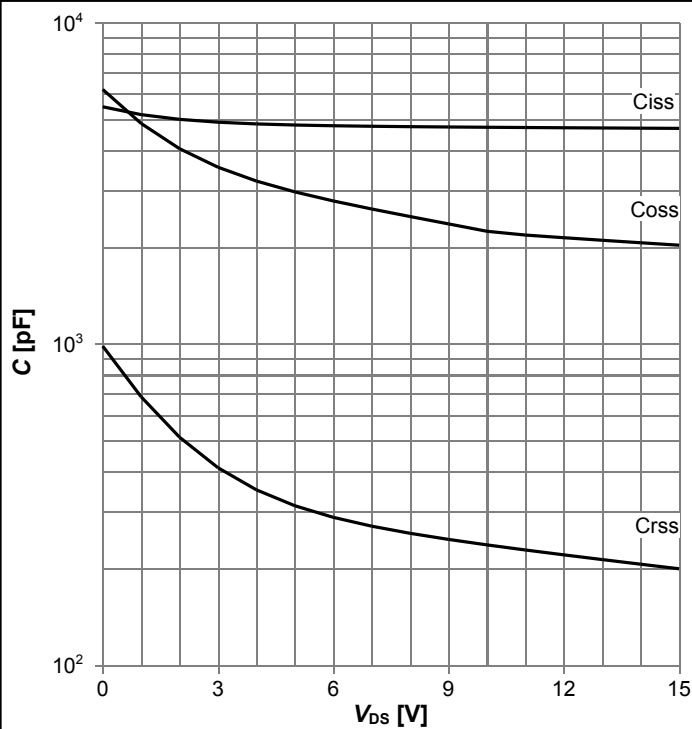
$R_{DS(on)}=f(T_j)$ ,  $I_D=30$  A; parameter:  $V_{GS}$

Diagram 10: Typ. gate threshold voltage



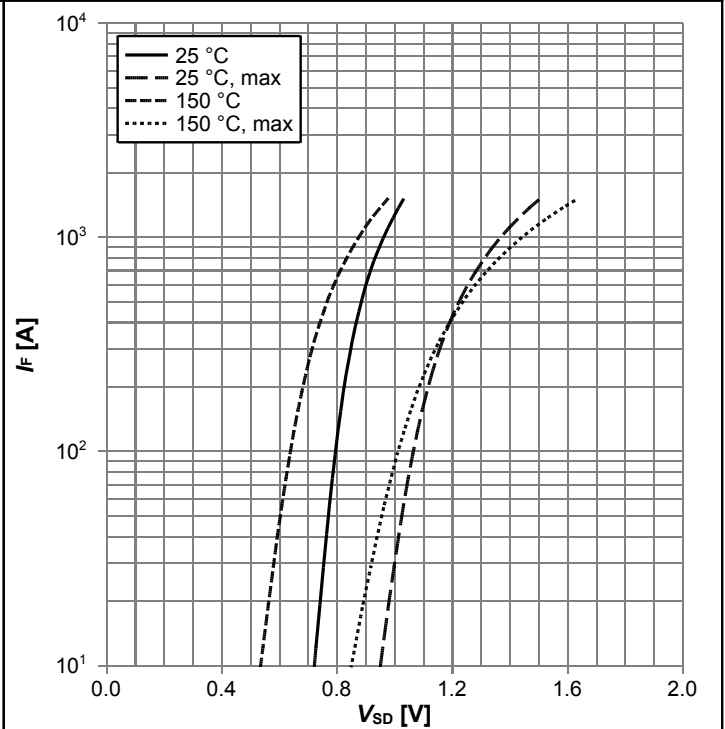
$V_{GS(th)}=f(T_j)$ ,  $V_{GS}=V_{DS}$ ; parameter:  $I_D$

Diagram 11: Typ. capacitances



$C=f(V_{DS})$ ;  $V_{GS}=0$  V;  $f=1$  MHz

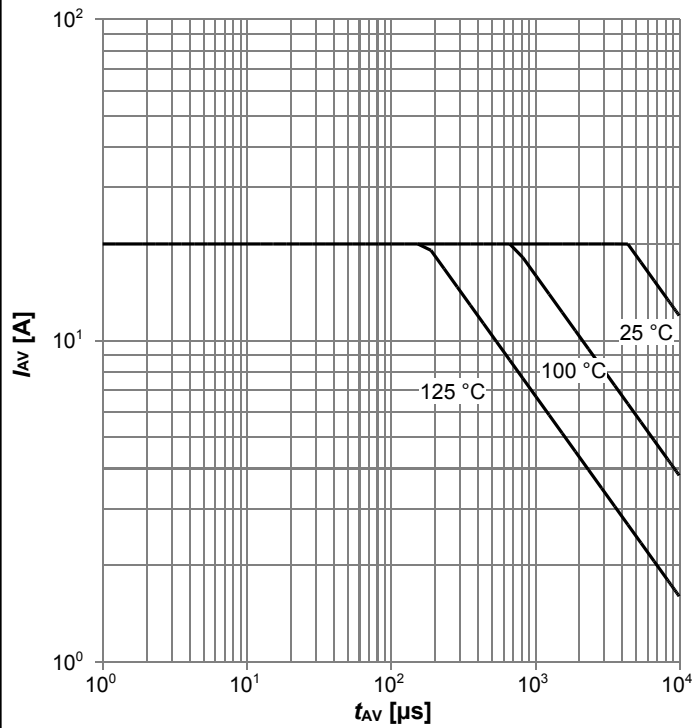
Diagram 12: Forward characteristics of reverse diode



$I_F=f(V_{SD})$ ; parameter:  $T_j$

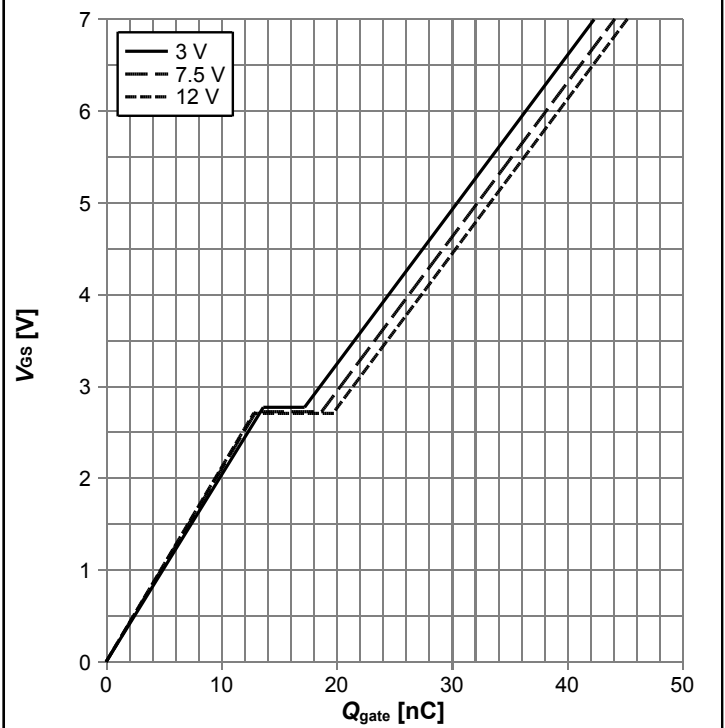


Diagram 13: Avalanche characteristics



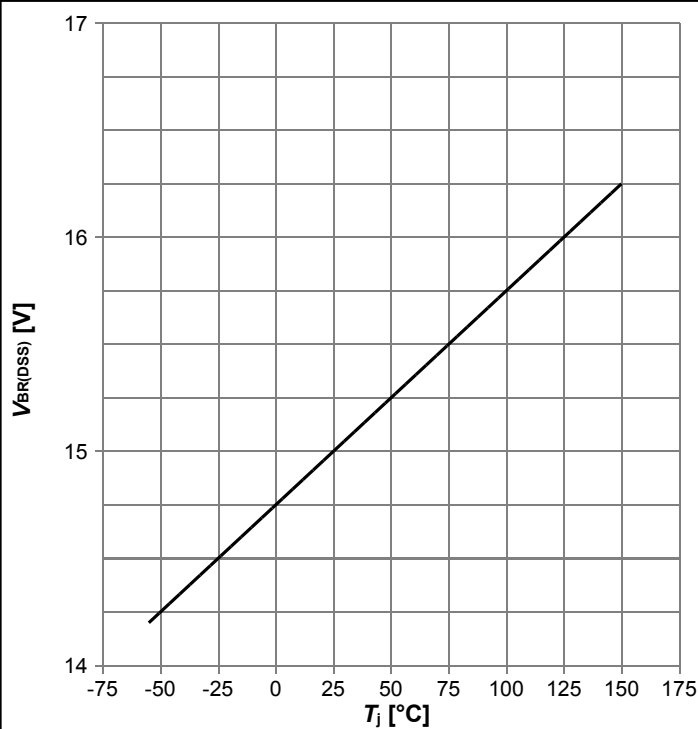
$I_{AS}=f(t_{AV})$ ;  $R_{GS}=25 \Omega$ ; parameter:  $T_{j,start}$

Diagram 14: Typ. gate charge



$V_{GS}=f(Q_{gate})$ ,  $I_D=30$  A pulsed,  $T_j=25$  °C; parameter:  $V_{DD}$

Diagram 15: Min. drain-source breakdown voltage

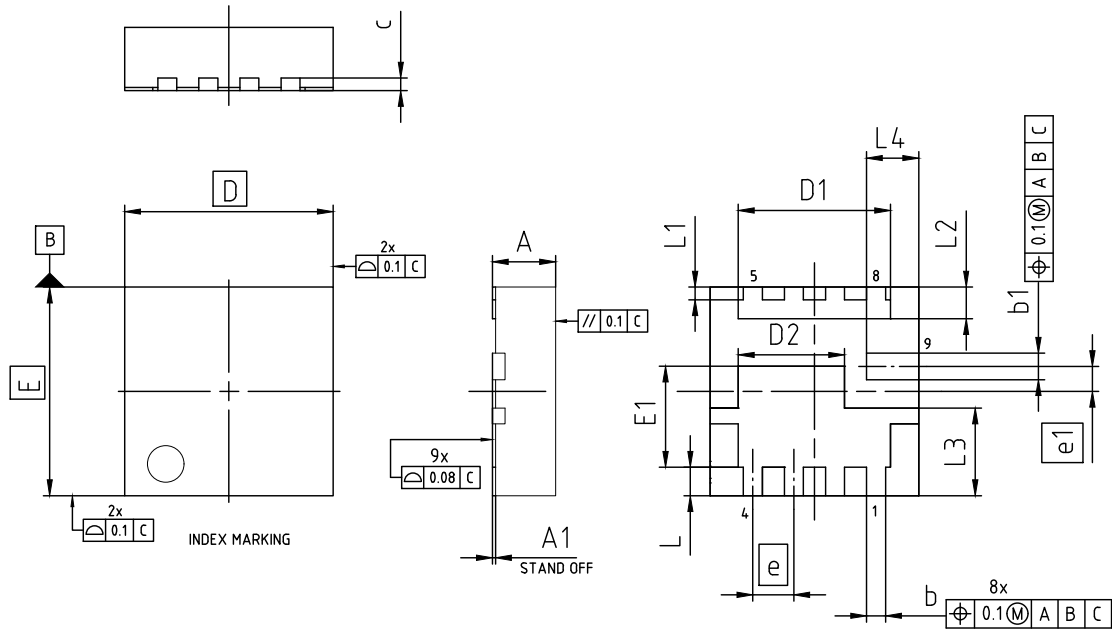


$V_{BR(DSS)}=f(T_j)$ ;  $I_D=1$  mA

Diagram Gate charge waveforms



## 5 Package Outlines



DIMENSION	MILLIMETERS	
	MIN.	MAX.
A	-	1.10
A1	-	0.05
b	0.20	0.40
b1	0.32	0.52
c	0.20	
D	3.30	
D1	2.31	2.51
D2	1.58	1.78
E	3.30	
E1	1.50	1.70
e	0.65	
e1	0.395	
L	0.35	0.55
L1	0.10	0.30
L2	0.40	0.60
L3	1.285	1.485
L4	0.73	0.93

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Figure 1 Outline PG-TTFN-9, dimensions in mm

## Revision History

IQE004NE1LM7CG

**Revision: 2023-07-25, Rev. 2.0**

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2023-07-25	Release of final version

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